



2SC3150

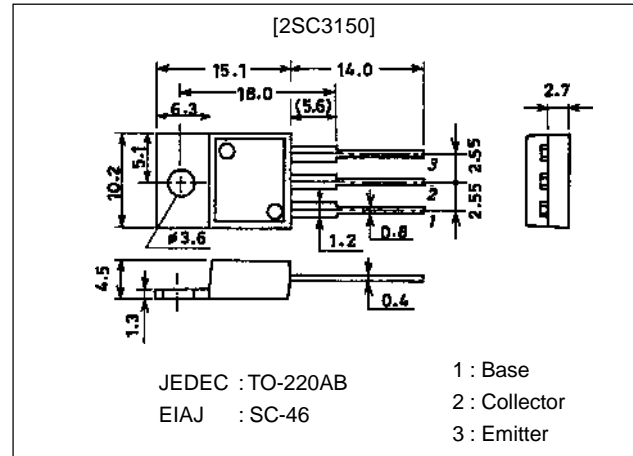
800V/3A Switching Regulator Applications

Features

- High breakdown voltage ($V_{CBO} \geq 900V$).
- Fast switching speed.
- Wide ASO.

Package Dimensions

unit:mm
2010C



Specifications

Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		900	V
Collector-to-Emitter Voltage	V_{CEO}		800	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		3	A
Collector Current (Pulse)	I_{CP}	$PW \leq 300\mu s$, Duty Cycle $\leq 10\%$	10	A
Base Current	I_B		1.5	A
Collector Dissipation	P_C	$T_c = 25^\circ C$	50	W
Junction Temperature	T_j		150	$^\circ C$
Storage Temperature	T_{stg}		-55 to +150	$^\circ C$

Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800V$, $I_E = 0$			10	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 5V$, $I_C = 0$			10	μA
DC Current Gain	h_{FE1}	$V_{CE} = 5V$, $I_C = 0.2A$	10*		40*	
	h_{FE2}	$V_{CE} = 5V$, $I_C = 1A$	8			
Gain-Bandwidth Product	f_T	$V_{CE} = 10V$, $I_C = 0.2A$		15		MHz
Output Capacitance	C_{ob}	$V_{CB} = 10V$, $f = 1MHz$		60		pF

* : The h_{FE1} of the 2SC3150 is classified as follows. When specifying the h_{FE1} rank, specify two ranks or more in principle.

10	K	20	15	L	30	20	M	40
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■ Any and all SANYO products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your SANYO representative nearest you before using any SANYO products described or contained herein in such applications.

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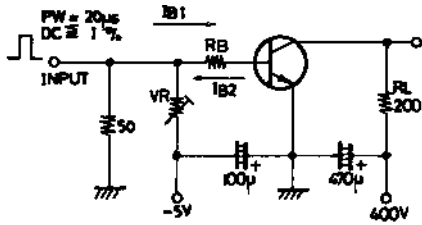
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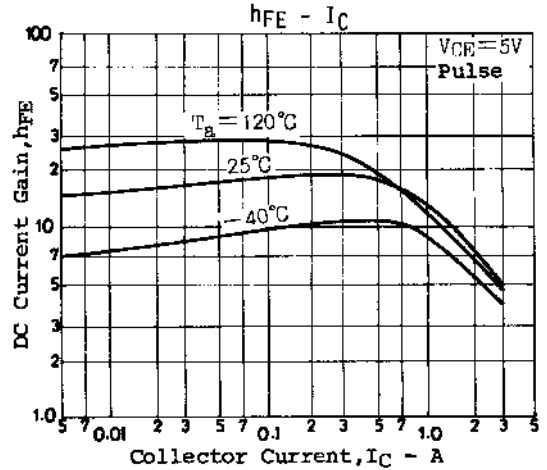
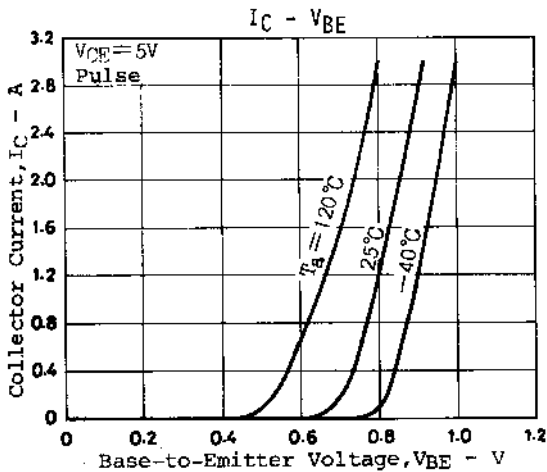
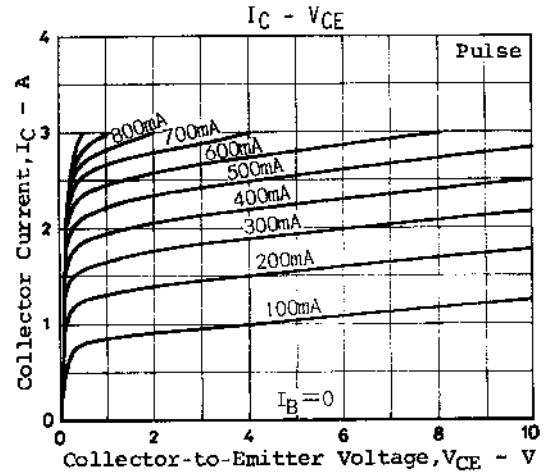
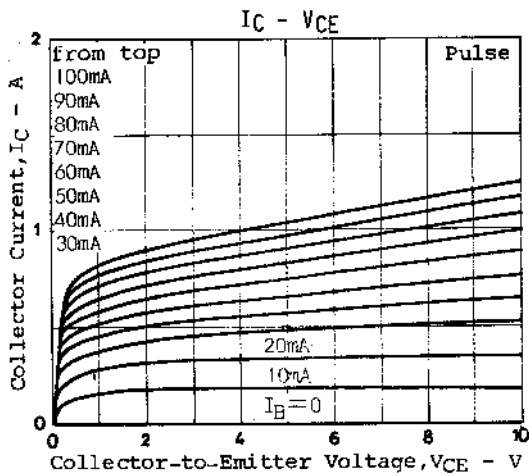
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=1.5A, I_B=0.3A$			2.0	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=1.5A, I_B=0.3A$			1.5	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	900			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	800			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Collector-to-Emitter Sustain Voltage	$V_{CEO(sus)}$	$I_C=3A, L=500\mu H, I_B=1A$	800			V
Collector-to-Emitter Sustain Voltage	$V_{CEX(sus)1}$	$I_C=1A, I_{B1}=0.2A, I_{B2}=-0.2A, L=2mH, \text{clamped}$	800			V
	$V_{CEX(sus)2}$	$I_C=0.5A, I_{B1}=0.1A, I_{B2}=-0.1A, L=5mH, \text{clamped}$	900			V
Turn-ON Time	t_{on}	$I_C=2A, I_{B1}=0.4A, I_{B2}=-0.8A, R_L=200\Omega, V_{CC}=400V$			1.0	μs
Storage Time	t_{stg}	$I_C=2A, I_{B1}=0.4A, I_{B2}=-0.8A, R_L=200\Omega, V_{CC}=400V$			3.0	μs
Fall Time	t_f	$I_C=2A, I_{B1}=0.4A, I_{B2}=-0.8A, R_L=200\Omega, V_{CC}=400V$			0.7	μs

Switching Time Test Circuit



Unit (resistance : Ω , capacitance : F)



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